

	Type	L #	Hits	Search Text	DBs	Time Stamp
1	BRS	L1	14	(re adj3 oxid\$10) same ("N.sub.2" adj8 "H.sub.2")	USPAT; US-PGP UB; EPO; JPO; DERWENT; IBM_TD_B	2002/08/27 19:39
2	BRS	L4	2	(re adj3 (oxidize or oxidized or oxidizing or oxidation)) same (rapid adj3 (thermal or anneal) same (nitrous or "N.sub.20" same "H.sub.2"))	USPAT; US-PGP UB; EPO; JPO; DERWENT; IBM_TD_B	2002/08/27 19:52
3	BRS	L8	40	"N.sub.20" adj3 "H.sub.2"	USPAT; US-PGP UB; EPO; JPO; DERWENT; IBM_TD_B	2002/08/27 20:26
4	BRS	L10	35	8 and (oxidize or oxidized or oxidizing or oxidation)	USPAT; US-PGP UB; EPO; JPO; DERWENT; IBM_TD_B	2002/08/27 20:27

	Type	L #	Hits	Search Text	DBs	Time Stamp
1	BRS	L1	14	(re adj3 oxid\$10) same ("N.sub.2" adj8 "H.sub.2")	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2002/08/27 19:39
2	BRS	L4	2	(re adj3 (oxidize or oxidized or oxidizing or oxidation)) same (rapid adj3 (thermal or anneal) same (nitrous or "N.sub.20" same "H.sub.2"))	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2002/08/27 19:52

	Type	L #	Hits	Search Text	DBs	Time Stamp
1	BRS	L1	31	((ultra adj3 thin) adj3 (silicon adj3 dioxide))	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2002/08/27 08:49
2	BRS	L11	39	@py <= "2001" and (re adj3 (oxid\$10) same H2)	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2002/08/27 09:23

	Type	L #	Hits	Search Text	DBs	Time Stamp
1	BRS	L1	31	((ultra adj3 thin) adj3 (silicon adj3 dioxide))	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2002/08/27 08:49

US-PAT-NO: 6114258

DOCUMENT-IDENTIFIER: US 6114258 A

TITLE: Method of oxidizing a substrate in the presence of nitride and oxynitride films

----- KWIC -----

A method of forming an oxide in the presence of a nitrogen-containing material is disclosed. In one embodiment, an oxygen-containing gas and a hydrogen-containing gas are provided to the chamber and reacted in the chamber. The reactive gases are used to oxidize the surface of a substrate in the chamber, the substrate having a nitrogen-containing material or a nitride film on a surface. In another embodiment, only an oxygen-containing gas, such as nitrous oxide ($N_{\cdot}sub\cdot2 O$) is used in the reoxidation reaction. According to the invention, the oxide is formed at the substrate and the nitrogen-containing material is displaced from the interface of the substrate and the oxide/nitrogen-containing material. By reacting an oxygen-containing gas with a hydrogen-containing gas in the chamber or "in situ," or by carrying out the reoxidation in an $N_{\cdot}sub\cdot2 O$ environment, the reoxidation reaction rapidly produces an oxide within an acceptable thermal budget.

The invention also relates to a dry oxygen-containing gas reoxidation process, wherein the oxygen-containing gas is nitrous oxide ($N_{\cdot}sub\cdot2 O$). Thus, in the processing system described in FIG. 11 and the accompanying text, control signal generation logic 450 would direct system controller 460 to carry out the

reoxidation process of the invention only in the presence of oxygen-containing gas 410, where oxygen-containing gas 410 is N._{sub.2} O, or the in the presence of N._{sub.2} O and another inert gas. Accordingly, system controller 460 would actuate mass flow controller 430 associated with hydrogen-containing gas 415 to close the valve associated with mass flow controller 430.

CLIPPEDIMAGE= JP02000124058A

PAT-NO: JP02000124058A

DOCUMENT-IDENTIFIER: JP 2000124058 A

TITLE: MULTILAYER CERAMIC CHIP CAPACITOR

PUBN-DATE: April 28, 2000

INVENTOR-INFORMATION:

NAME	COUNTRY
ABE, MICHIRO	N/A
NOMURA, TAKESHI	N/A
SUMITA, NARIKAZU	N/A
NISHIYAMA, TSUGUSUKE	N/A
NAKANO, YUKIE	N/A
IKEDA, MASAAKI	N/A

ASSIGNEE-INFORMATION:

NAME	COUNTRY
TDK CORP	N/A

APPL-NO: JP11252052

APPL-DATE: October 18, 1989

INT-CL (IPC): H01G004/12;C04B035/49 ;H01B003/12

ABSTRACT:

PROBLEM TO BE SOLVED: To obtain a multilayer chip capacitor whose service life is long and reliability is superior by constituting the inner electrode material which is nickel or a nickel alloy and a dielectric material in a laminated state, baking the materials in a neutral or reducing atmosphere, and thermally treating the materials in a neutral or weak reducing atmosphere.

SOLUTION: In a multilayer chip capacitor 1, inner electrodes 21, 25 and dielectric layers 3 are laminated alternately, and a pair of outer electrodes

51, 55 are connected with the respective inner electrodes 21, 25. In this case, the inner electrodes 21, 25 are formed of Ni or Ni alloy. After that, baking is performed. In order to have the dielectric layer 3 re-oxidized, thermal treatment is performed. In the baking, a neutral or reducing atmosphere, especially a moistened mixture gas of N₂ and H₂ or the like is used as the gas for the reducing atmosphere. It is preferable that a heat treatment be performed at 900-1,200

COPYRIGHT: (C) 2000, JPO